#### **Features**

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching
- Positive Temperature Coefficient on V<sub>F</sub>
- Increased Creepage/Clearance Distance

#### **Benefits**

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

### **Applications**

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters





Part Number	Package	Marking
HC4D20120H	TO247-2L	HC4D20120H

### Maximum Ratings (T<sub>c</sub>=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	1200	V		
V <sub>RSM</sub>	Surge Peak Reverse Voltage	1300	V		
V <sub>R</sub>	DC Peak Reverse Voltage	1200	V		
I <sub>F</sub>	Continuous Forward Current	54 26 20	А	T <sub>c</sub> =25°C T <sub>c</sub> =135°C T <sub>c</sub> =156°C	Fig. 3
I <sub>FRM</sub>	Repetitive Peak Forward Surge Current	86 56	А	$T_c$ =25°C, $t_p$ =10 ms, Half Sine Pulse $T_c$ =110°C, $t_p$ =10 ms, Half Sine Pulse	
I <sub>FSM</sub>	Non-Repetitive Forward Surge Current	130 104	А	$T_c$ =25°C, $t_p$ =10 ms, Half Sine Pulse $T_c$ =110°C, $t_p$ =10 ms, Half Sine Pulse	Fig. 8
I <sub>F,Max</sub>	Non-Repetitive Peak Forward Current	1150 950	А	$T_c$ =25°C, $t_p$ =10 $\mu$ s, Pulse $T_c$ =110°C, $t_p$ =10 $\mu$ s, Pulse	Fig. 8
P <sub>tot</sub>	Power Dissipation	246 106.5	W	T <sub>c</sub> =25°C T <sub>c</sub> =110°C	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	V <sub>R</sub> =0-960V	
∫i²dt	i²t value	84.5 54	A <sup>2</sup> s	$T_c$ =25°C, $t_p$ =10 ms $T_c$ =110°C, $t_p$ =10 ms	
T <sub>J</sub> , T <sub>stg</sub>	Operating Junction and Storage Temperature	-55 to +175	°C		
	TO-247 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	







### **Electrical Characteristics**

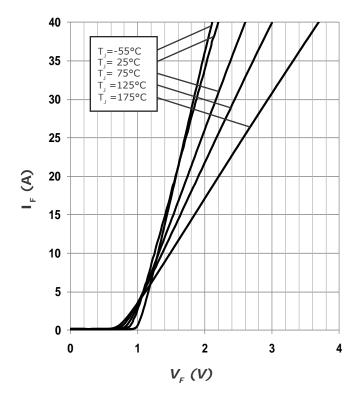
Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V <sub>F</sub>	Forward Voltage	1.5 2.2	1.8 3	V	$I_F = 20 \text{ A } T_J = 25^{\circ}\text{C}$ $I_F = 20 \text{ A } T_J = 175^{\circ}\text{C}$	Fig. 1
$I_R$	Reverse Current	35 65	200 400	μΑ	$V_R = 1200 \text{ V } T_J = 25^{\circ}\text{C}$ $V_R = 1200 \text{ V } T_J = 175^{\circ}\text{C}$	Fig. 2
Q <sub>c</sub>	Total Capacitive Charge	99		nC	$V_R = 800 \text{ V}, I_F = 20\text{A} \\ di/dt = 200 \text{ A}/\mu\text{s} \\ T_J = 25^{\circ}\text{C}$	Fig. 5
С	Total Capacitance	1500 93 67		pF	$V_R = 0 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 400 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 800 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$	Fig. 6
E <sub>c</sub>	Capacitance Stored Energy	28		µJ	V <sub>R</sub> = 800 V	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

#### **Thermal Characteristics**

Symbol Parameter		Тур.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.61	°C/W	Fig. 9

## **Typical Performance**





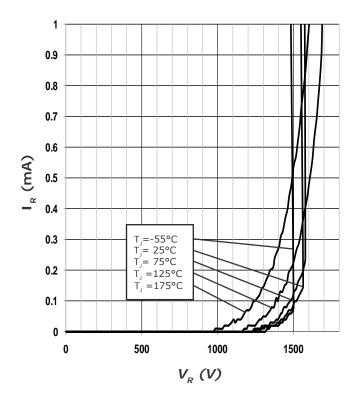


Figure 2. Reverse Characteristics



## **Typical Performance**

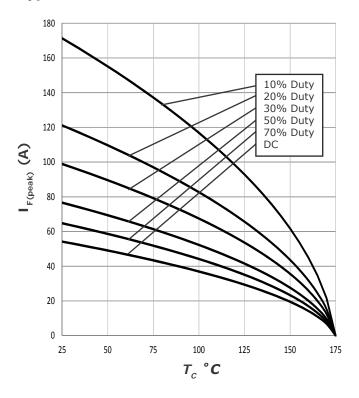


Figure 3. Current Derating

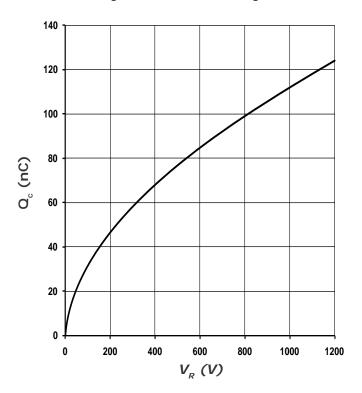


Figure 5. Recovery Charge vs. Reverse Voltage

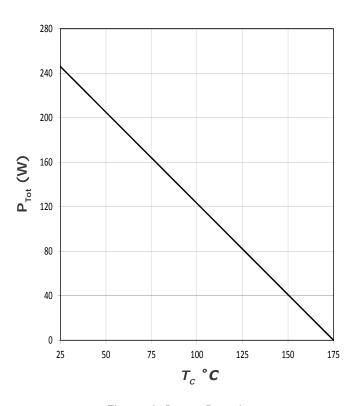


Figure 4. Power Derating

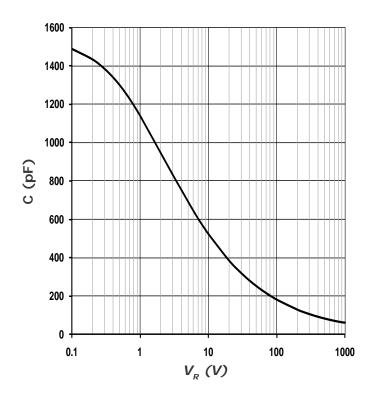
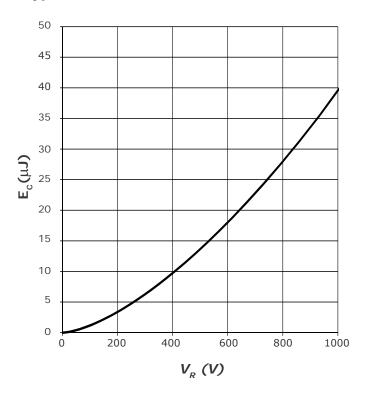


Figure 6. Capacitance vs. Reverse Voltage



### **Typical Performance**



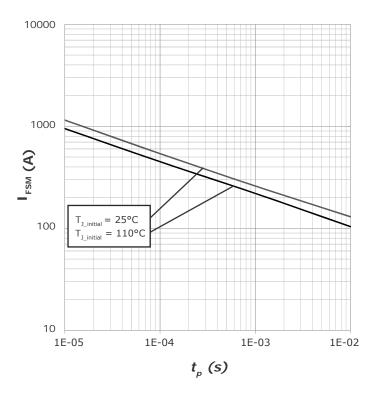


Figure 7. Typical Capacitance Stored Energy

Figure 8. Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform)

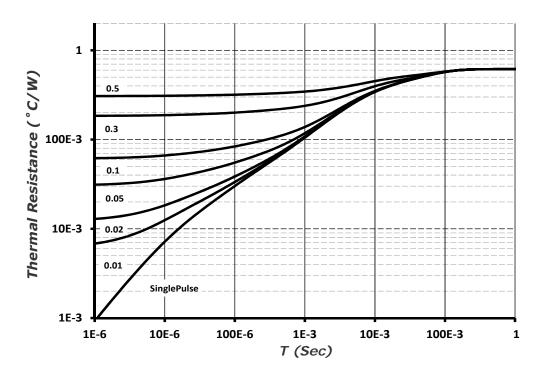


Figure 9. Transient Thermal Impedance

### **Diode Model**

$$\begin{array}{c|c} - & & \\ \hline - & & \\ - & & \\ \hline - & & \\ - & & \\ \hline - & & \\ - & & \\ \hline - & & \\ - & & \\ \hline - & & \\ - & & \\ \hline - & & \\ - & & \\ \hline - & & \\ - & & \\ \hline - & & \\ - & & \\ \hline - & & \\ - & & \\ \hline - & &$$

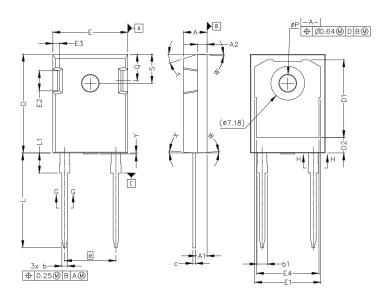
$$V_{fT} = V_T + If * R_T$$

$$V_T = 0.97 + (T_J^* - 1.40^*10^{-3})$$
  
 $R_T = 0.023 + (T_J^* 2.71^*10^{-4})$ 

Note:  $T_j$  = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

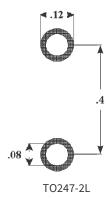
# **Package Dimensions**

Package: TO247-2L All dimensions in mm.



0)44	MILLIMETERS		INCHES		
SYM	MIN	MAX	MIN	MAX	
A	4.83	5.21	.190	.205	
A1	2.29	2.54	.090	.100	
A2	1.91	2.16	.075	.085	
b'	1.07	1.28	.042	.050	
b	1.07	1.33	.042	.052	
b1	1.91	2.41	.075	.095	
b2	1.91	2.16	.075	.085	
c'	0.55	0.65	.022	.026	
с	0.55	0.68	.022	.027	
D	20.80	21.10	.819	.831	
D1	16.25	17.35	.640	.683	
D2	2.86	3.16	.112	.124	
Е	15.75	16.13	.620	.635	
E1	13.10	14.15	.516	.557	
E2	3.68	5.10	.145	.201	
E3	1.00	1.90	.039	.075	
E4	12.38	13.43	.487	.529	
e	10.88	BSC	.428 BSC		
L	19.81	20.32	.780	.800	
L1	4.10	4.40	.161	.173	
φP	3.51	3.65	.138	.144	
Q	5.49	6.00	.216	.236	
S	6.04	6.30	.238	.248	
T		17.5° REF.			
W		3.5° RI	EF.		
X		4° REF.			
Y	0	0.50	0	0.020	

# **Recommended Solder Pad Layout**



all units are in inches

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